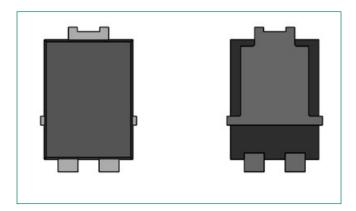
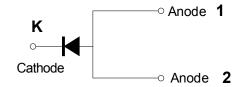
Schottky Barrier Rectifier DST860S-A, 8A, 60V, TO-277B, Single

DST860S-A HF RoHS 10 (3)



Pin out



Description

Littelfuse DST series Ultra Low $V_{\scriptscriptstyle F}$ Schottky Barrier Rectifier is designed to meet the general requirements of commercial and industrial applications by providing high temperature, low leakage and lower $V_{\scriptscriptstyle E}$ products.

It is suitable for high frequency switching mode power supply, free-wheeling diodes and polarity protection diodes.

Features

- High reliability application and AEC-Q101 qualified
- Ultra low forward voltage drop
- High frequency operation
- MSL: Level 1 unlimited
- High junction temperature capability
- Trench MOS Schottky technology

- Single die in TO-277B Package
- Pb-free E3 means 2nd level interconnect is Pb-free and the terminal finish material is tin(Sn) (IPC/ JEDEC J-STD-609A.01)

Applications

- Switching mode power supply
- DC/DC converters
- Free-Wheeling diodes
- Polarity Protection Diodes

Maximum Ratings

Parameters	Symbol	Test Conditions	Max	Unit
Peak Inverse Voltage	V _{RWM}	-	60	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _L = 125 °C rectangular wave form	8	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	140	А

Electrical Characteristics

Parameters	Symbol	Symbol Test Conditions		Max	Unit	
Forward Voltage Drop*	V _{F1}	@4A, Pulse, T _J = 25 °C	0.42	-	-	
		@8A, Pulse, T _J = 25 °C	0.50	0.61	V	
	V _{F2}	@4A, Pulse, T _J = 125 °C	0.34	-		
		@8A, Pulse, T _J = 125 °C	0.44	0.55		
Reverse Current*	I _{R1}	$@V_R = rated V_R, T_J = 25 °C$	0.02	0.6	^	
	I _{R2}	$@V_R = rated V_{R,} T_J = 125 ^{\circ}C$	10	25	mA mA	
Junction Capacitance	C_{T}	$@V_R = 5V, T_C = 25 ^{\circ}C, f_{SIG} = 1MHz$	502	-	pF	

^{*} Pulse Width < 300µs, Duty Cycle <2%

Schottky Barrier Rectifier DST860S-A, 8A, 60V, TO-277B, Single

Thermal-Mechanical Specifications

Parameters	Symbol	Test Conditions	Max	Unit
Junction Temperature	T _J		-55 to +150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Maximum Thermal Resistance Junction to Ambient	R _{thJA}	DC arresting	75	°C/W
Maximum Thermal Resistance Junction to Lead	R _{thJL}	DC operation	4	°C/W
Approximate Weight	wt		0.08	g
Case Style	TO-277B			

Figure 1: Typical Forward Characteristics

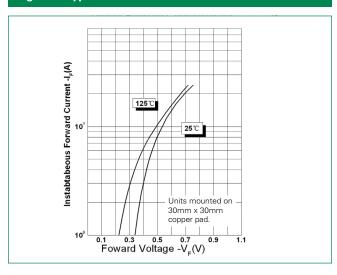


Figure 2: Typical Reverse Characteristics

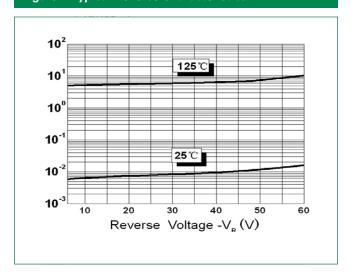
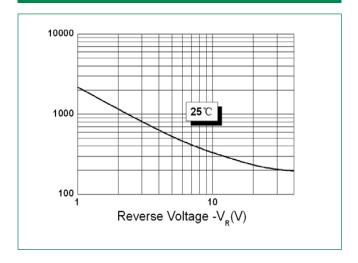
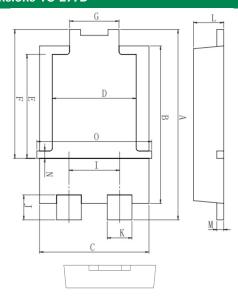


Figure 3: Typical Junction Capacitance



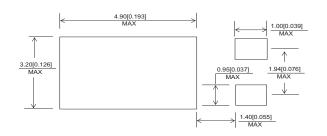
Schottky Barrier Rectifier DST860S-A, 8A, 60V, TO-277B, Single

Dimensions-TO-277B



Symbol	Millimeters			
Symbol	Min	Тур	Max	
А	6.30	6.50	6.70	
В	5.28	5.38	5.48	
С	3.88	3.98	4.08	
D	2.90	3.05	3.20	
E	3.40	3.55	3.70	
F	4.20	4.40	4.60	
G	1.70	1.80	1.90	
I	1.74	1.84	1.94	
J	0.65	0.85	1.05	
K	0.85	0.90	0.95	
L	0.95	1.10	1.25	
М	0.20	0.25	0.30	
N	0.25	0.40	0.55	
0	4.00	4.05	4.25	

Mounting Pad Layout



Packing Options					
Part Number	Marking	Packing Mode	M.O.Q		
DST860S-A	DST860S-A	5000pcs / Reel	5000		

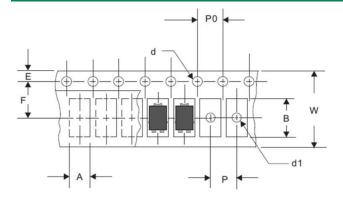
Part Numbering and Marking System



DST = Device Type
10 = Forward Current (10A)
8 0 = Reverse Voltage(8A) V)
60 = Package Type (60V)
C = AEC-Q101 qualified device
LF = Littelfuse

LF = Littelfuse YY = Year WW = Week L = Lot Number

Carrier Tape & Reel Specification



Symbol	Millimeters		
	Min	Max	
А	4.28	4.48	
В	6.80	7.00	
d	1.40	1.60	
d1	-	1.50	
Е	1.65	1.85	
F	5.40	5.60	
Р	7.90	8.10	
P0	3.90	4.10	
W	11.70	12.30	

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Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications.

Read complete Disclaimer Notice at http://www.littelfuse.com/disclaimer-electronics.



Part of:

